

UT54LVDS217 Serializer



FEATURES

- ❑ 15 to 75 MHz shift clock support
- ❑ Low power consumption
- ❑ Power-down mode <200 μ W (max)
- ❑ Cold sparing all pins
- ❑ Narrow bus reduces cable size and cost
- ❑ Up to 1.575 Gbps throughput
- ❑ Up to 197 Megabytes/sec bandwidth
- ❑ 325 mV (typ) swing LVDS devices for low EMI
- ❑ PLL requires no external components
- ❑ Rising edge strobe
- ❑ Radiation-hardened design; total dose irradiation testing to MIL-STD-883 Method 1019
 - Total-dose: 300 krad(Si)
 - Latchup immune (LET > 100 MeV-cm²/mg)
- ❑ Packaging options:
 - 48-lead flatpack
- ❑ Standard Microcircuit Drawing TBD
 - QML Q and V compliant part
- ❑ Compatible with TIA/EIA-644 LVDS standard

INTRODUCTION

The UT54LVDS217 Serializer converts 21 bits of CMOS/TTL data into three LVDS (Low Voltage Differential Signaling) data streams. A phase-locked transmit clock is transmitted in parallel with the data streams over a fourth LVDS link. Every cycle of the transmit clock 21 bits of input data are sampled and transmitted.

At a transmit clock frequency of 75 MHz, 21 bits of TTL data are transmitted at a rate of 525 Mbps per LVDS data channel. Using a 75 MHz clock, the data throughput is 1.575 Gbit/s (197 Mbytes/sec).

The UT54LVDS217 Serializer allows the use of wide, high speed TTL interfaces while reducing overall EMI and cable size.

All pins have Cold Spare buffers. These buffers will be high impedance when V_{DD} is tied to V_{SS} .

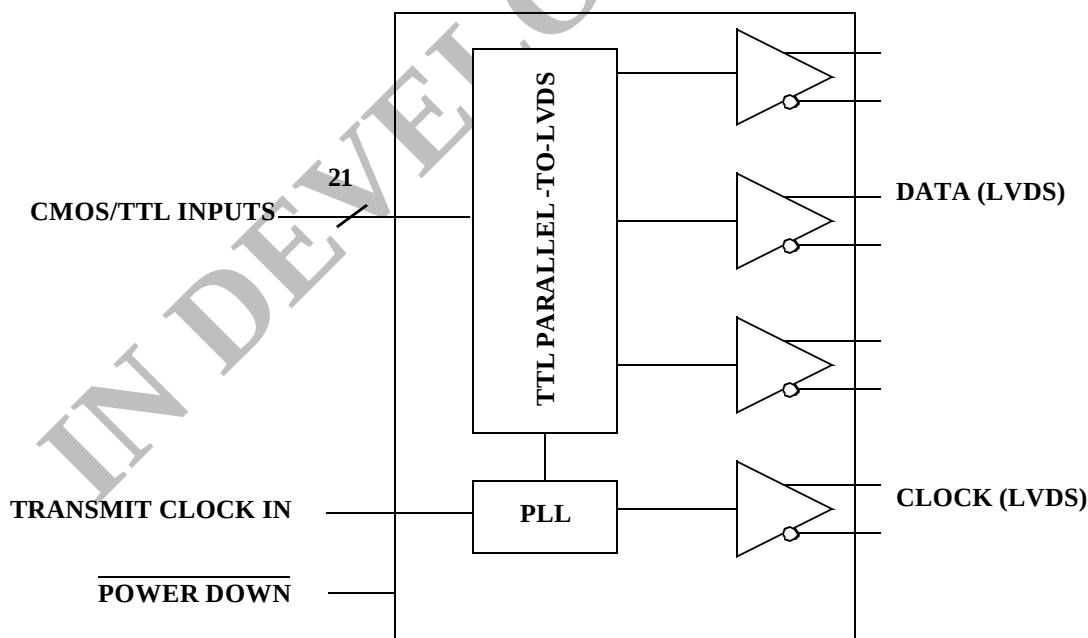


Figure 1. UT54LVDS217 Serializer Block Diagram

TxIN4	1	48	TxIN3
V _{DD}	2	47	TxIN2
TxIN5	3	46	GND
TxIN6	4	45	TxIN1
GND	5	44	TxIN0
TxIN7	6	43	N/C
TxIN8	7	42	LVDS GND
V _{DD}	8	41	TxOUT0-
TxIN9	9	40	TxOUT0+
TxIN10	10	39	TxOUT1-
GND	11	38	TxOUT1+
TxIN11	12	37	LVDS V _{DD}
TxIN12	13	36	LVDS GND
V _{DD}	14	35	TxOUT2-
TxIN13	15	34	TxOUT2+
TxIN14	16	33	TxCLK OUT-
GND	17	32	TxCLK OUT+
TxIN15	18	31	LVDS GND
TxIN16	19	30	PLL GND
TxIN17	20	29	PLL V _{DD}
V _{DD}	21	28	PLL GND
TxIN18	22	27	PWR DWN
TxIN19	23	26	TxCLK IN
GND	24	25	TxIN20

PIN DESCRIPTION

Pin Name	I/O	No.	Description
TxIN	I	21	TTL level input
TxOUT+	O	3	Positive LVDS differential data output
TxOUT-	O	3	Negative LVDS differential data output
TxCLK IN	I	1	TTL level clock input. The rising edge acts as data strobe. Pin name TxCLK IN
TxCLK OUT+	O	1	Positive LVDS differential clock output
TxCLK OUT-	O	1	Negative LVDS differential clock output
PWR DWN	I	1	TTL level input. Assertion (low input) TRI-STATES the clock and data outputs, ensuring low current at power down.
V _{DD}	I	4	Power supply pins for TTL inputs and logic
GND	I	5	Ground pins for TTL inputs and logic
PLL V _{DD}	I	1	Power supply pins for PLL
PLL GND	I	2	Ground pins for PPL
LVDS V _{DD}	I	1	Power supply pin for LVDS output
LVDS GND	I	3	Ground pins for LVDS outputs

Figure 2. UT54LVDS217 Pinout

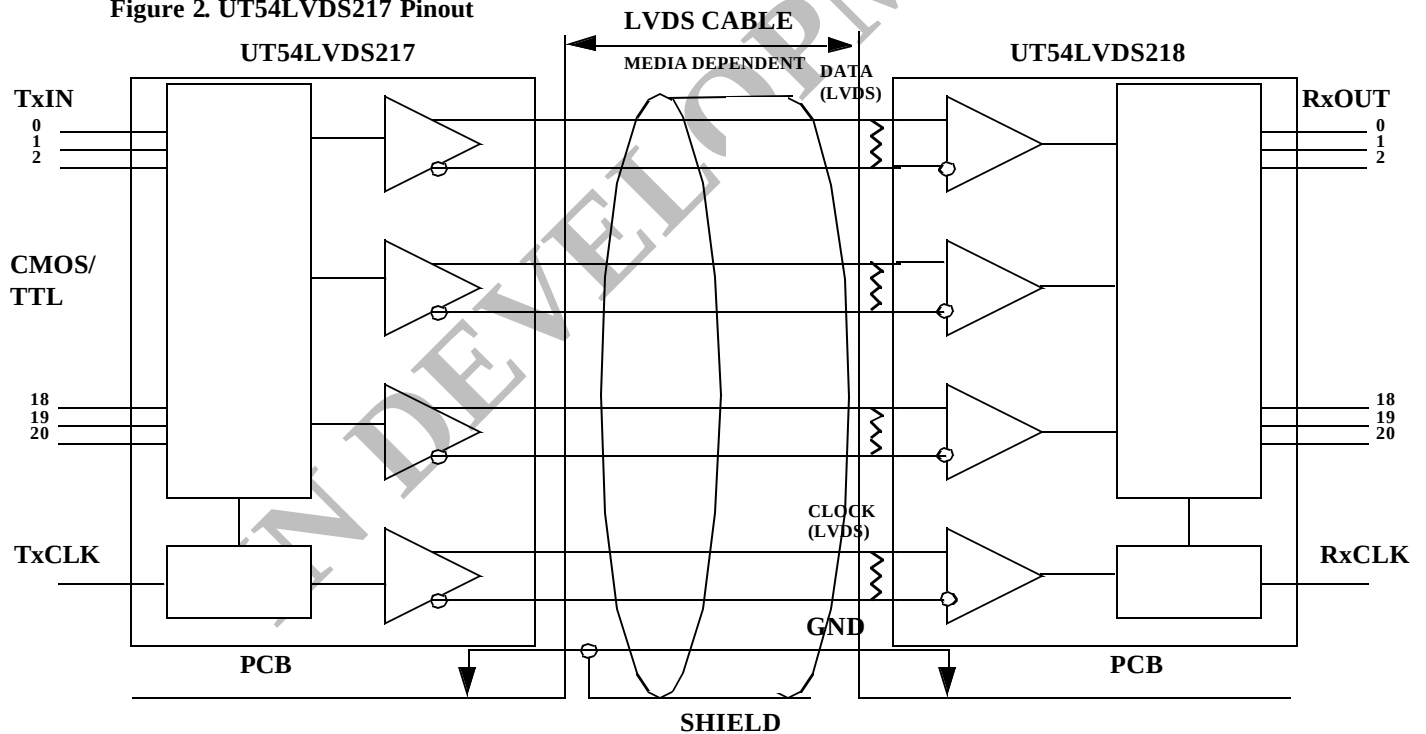


Figure 3. UT54LVDS217 Typical Application

ABSOLUTE MAXIMUM RATINGS¹(Referenced to V_{SS})

SYMBOL	PARAMETER	LIMITS
V_{DD}	DC supply voltage	-0.3 to 4.0V
$V_{I/O}$	Voltage on any pin	-0.3 to ($V_{DD} + 0.3V$)
T_{STG}	Storage temperature	-65 to +150°C
P_D	Maximum power dissipation	2 W
T_J	Maximum junction temperature ²	+150°C
Θ_{JC}	Thermal resistance, junction-to-case ³	10°C/W
I_I	DC input current	±10mA

Notes:

1. Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions beyond limits indicated in the operational sections of this specification is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability and performance.
2. Maximum junction temperature may be increased to +175°C during burn-in and lifetest.
3. Test per MIL-STD-883, Method 1012.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS
V_{DD} , P_{LL} V_{DD} , LVDS V_{DD}	Positive supply voltage	3.0 to 3.6V
T_C	Case temperature range	-55 to +125°C
V_{IN}	DC input voltage	0V to V_{DD}

DC ELECTRICAL CHARACTERISTICS¹(V_{DD} = 3.3V-0.3V; -55°C < T_C < +125°C)

SYMBOL	PARAMETER	CONDITION	MIN	MAX	UNIT
CMOS/TTL DC SPECIFICATIONS (EN)					
V _{IH}	High-level input voltage	V _{DD} = 3.0V or 3.6V	2.0	V _{DD}	V
V _{IL}	Low-level input voltage	V _{DD} = 3.0V or 3.6V	GND	0.8	V
I _{IH}	High-level input current	V _{IN} = 3.6V; V _{DD} = 3.6V	-10	+10	μA
I _{IL}	Low-level input current	V _{IN} = 0V; V _{DD} = 3.6V	-10	+10	μA
V _{CL}	Input clamp voltage	I _{CL} = -18mA		-1.5	V
I _{CS}	Cold Spare Leakage current	V _{IN} = 3.6V; V _{DD} = V _{SS}	-20	+20	μA
LVDS OUTPUT DC SPECIFICATIONS (OUT+, OUT-)					
V _{OD} ⁵	Differential Output Voltage	R _L = 100Ω (See Figure 14)	250	400	mV
ΔV _{OD} ⁵	Change in V _{OD} between complimentary output states	R _L = 100Ω (See Figure 14)		35	mV
V _{OS} ⁵	Offset Voltage	R _L = 100Ω, $(V_{OS} = \frac{V_{OH} + V_{OL}}{2})$	1.075	1.400	V
ΔV _{OS} ⁵	Change in V _{OS} between complimentary output states	R _L = 100Ω		35	mV
I _{OZ} ⁴	Output Three-State Current	PWR DWN = 0V V _{OUT} = 0V or V _{DD}	-10	+10	μA
I _{CSOUT}	Cold Spare Leakage Current	V _{OUT} = 3.6V, V _{DD} = V _{SS}	-20	+20	μA
I _{OS} ^{2,3}	Output Short Circuit Current	V _{OUT} ⁺ or V _{OUT} ⁻ = 0V		5mA	mA
Supply Current					
I _{CCL} ⁴	Transmitter supply current with loads	R _L = 100Ω all channels (figure 4) CL = 5pF, f = 75MHz		65.0	mA
I _{CCZ} ^{4,6}	Power down current	D _{IN} = V _{DD} or V _{SS} PWR DWN = 0V, f = 0Hz		60.0	μA

Notes:

- Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground.
- Output short circuit current (I_{OS}) is specified as magnitude only, minus sign indicates direction only. Only one output should be shorted at a time, do not exceed maximum junction temperature specification.
- Guaranteed by characterization.
- Devices are tested @ 3.6V only.
- Clock outputs guaranteed by design.
- Post 100Krad, I_{CCZ} = 200μA, post 300Krad, I_{CCZ} = 700μA.

AC SWITCHING CHARACTERISTICS¹
(V_{DD} = 3.0V to 3.6V; TA = -55°C to +125°C)

SYMBOL	PARAMETER	MIN	MAX	UNIT
LLHT ²	LVDS Low-to-High Transition Time (Figure 5)		1.5	ns
LHLT ²	LVDS High-to-Low Transition Time (Figure 5)		1.5	ns
TPPos0	Transmitter Output Pulse Position for Bit 0 (Figure 13) f=75MHz	0.25	0.85	ns
TPPos1	Transmitter Output Pulse Position for Bit 1(Fgiure 13) f=75MHz	2.15	2.75	ns
TPPos2	Transmitter Output Pulse Position for Bit 2 (Figure 13) f=75MHz	4.05	4.65	ns
TPPos3	Transmitter Output Pulse Position for Bit 3(Fgiure 13) f=75MHz	5.95	6.55	ns
TPPos4	Transmitter Output Pulse Position for Bit 4 (Figure 13) f=75MHz	7.85	8.45	ns
TPPos5	Transmitter Output Pulse Position for Bit 5 (Figure 13) f=75MHz	9.75	10.35	ns
TPPos6	Transmitter Output Pulse Position for Bit 6 (Figure 13) f=75MHz	11.65	12.25	ns
TCCS ³	Channel to Channel skew (Figure 8)		0.6	ns
TCIP	TxCLK IN Period (Figure 8)	13.33	66.7	ns
TCIH ⁴	TxCLK IN High Time (Figure 8)	0.35Tcip	0.65Tcip	ns
TCIL ⁴	TxCLK IN Low Time (Figure 8)	0.35Tcip	0.65Tcip	ns
TSTC ²	TxIN Setup to TxCLK IN (Figure 8) f=75MHz	2.5		ns
THTC ²	TxIN Hold to TxCLK IN (Figure 8) f=75MHz	1.5		ns
TCCD	TxCLK IN to TxCLK OUT Delay (Figure 9)	0.5	2.5	ns
TPLLS	Transmitter Phase Lock Loop Set (Figure 10)		10	ms
TPDD	Transmitter Powerdown Delay (Figure 12)		100	ns

Notes:

1. Recommend transistion time for TXCLK In is 1.0 to 6.0 ns (figure 6).
2. Guaranteed by characterization.
3. Channel to channel skew is defined as the difference between TPPOS max limit and TPPOS minimum limit.
4. Guaranteed by design.

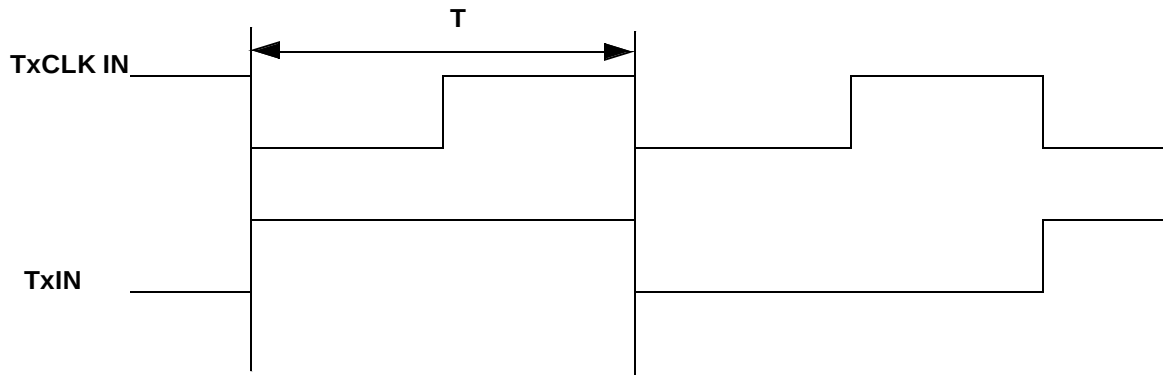


Figure 4. Test Pattern

AC TIMING DIAGRAMS

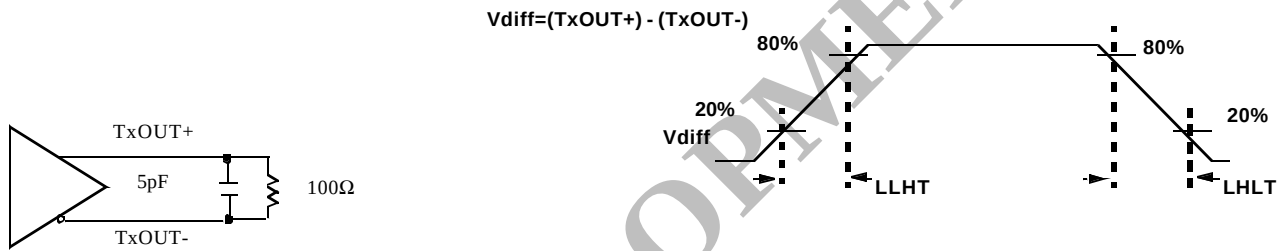


Figure 5. UT54LVDS217 Output Load and Transition Times

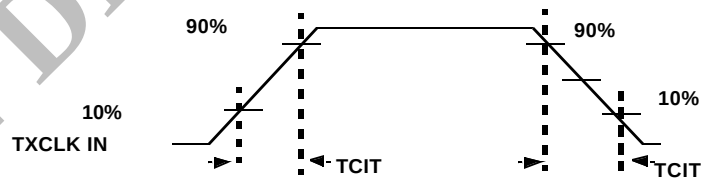
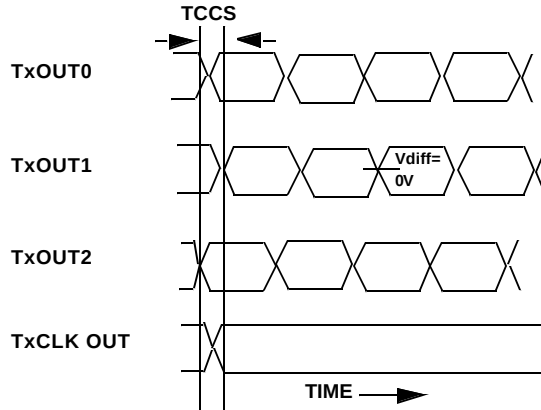


Figure 6. UT54LVDS217 Input Clock Transition Time



Notes:

1. Measurements at $V_{DIFF} = 0V$
2. TCCS measured between earliest and latest LVDS edges.
3. TxCLK Differential Low-High Edge.

Figure 7. UT54LVDS217 Channel-to-Channel Skew

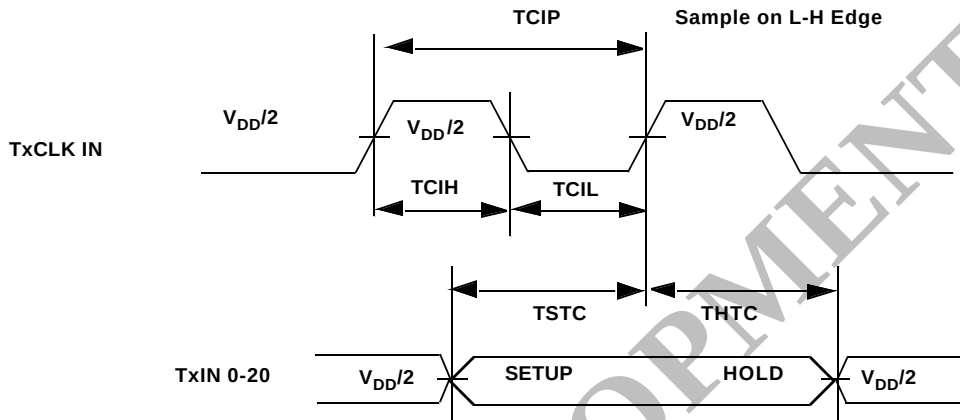


Figure 8. UT54LVDS217 Setup/Hold and High/Low Times

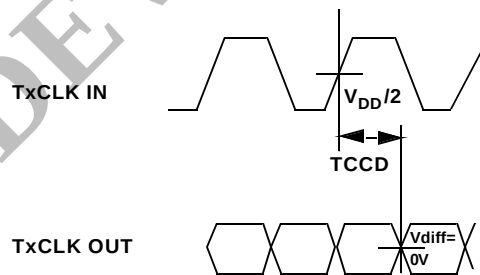


Figure 9. UT54LVDS217 Clock-to-Clock Out Delay

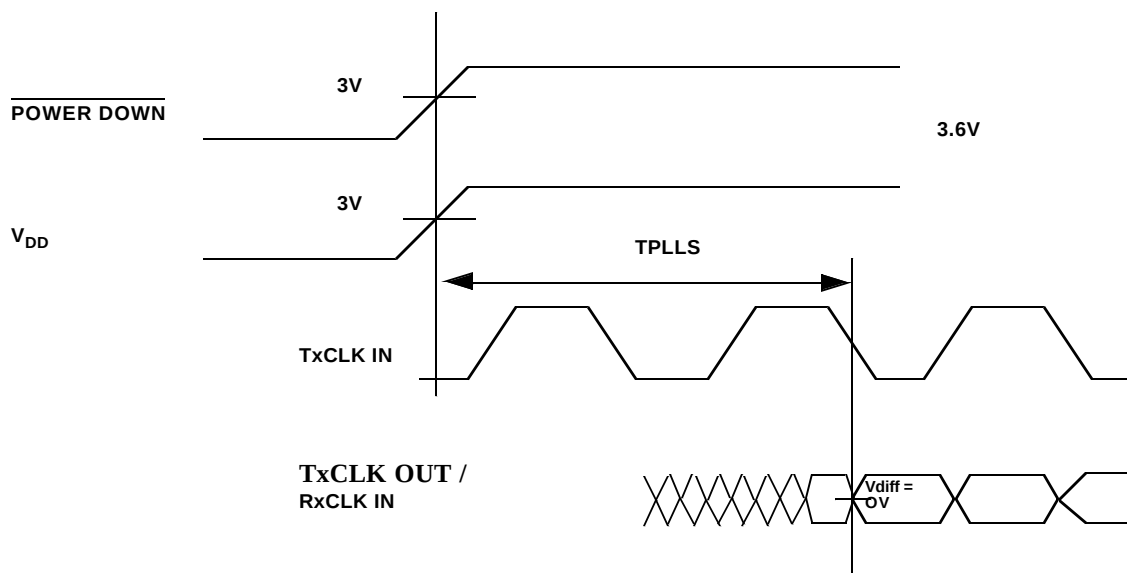


Figure 10. UT54LVDS217 Phase Lock Loop Set Time

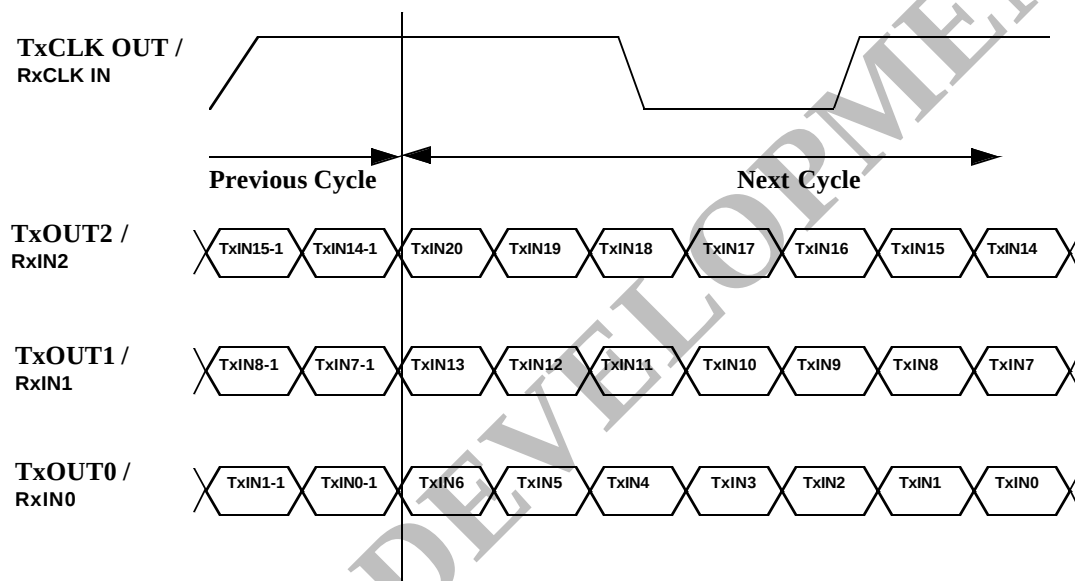


Figure 11. UT54LVDS217 Parallel TTL Data Inputs Mapped to LVDS Outputs

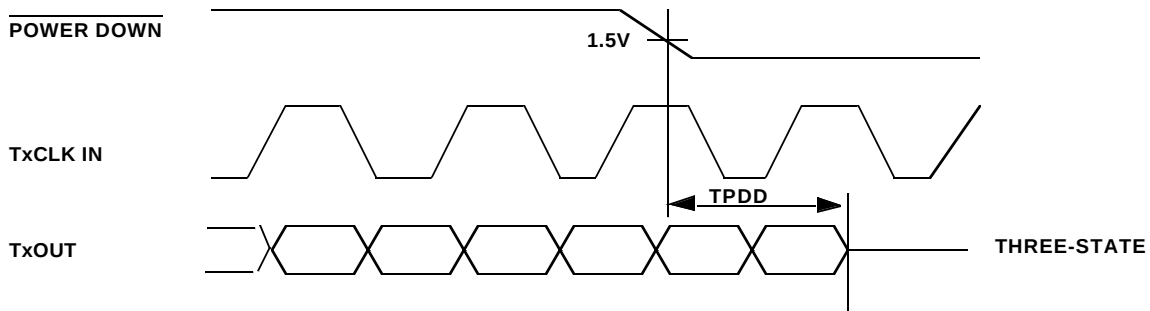


Figure 12. Transmitter Powerdown Delay

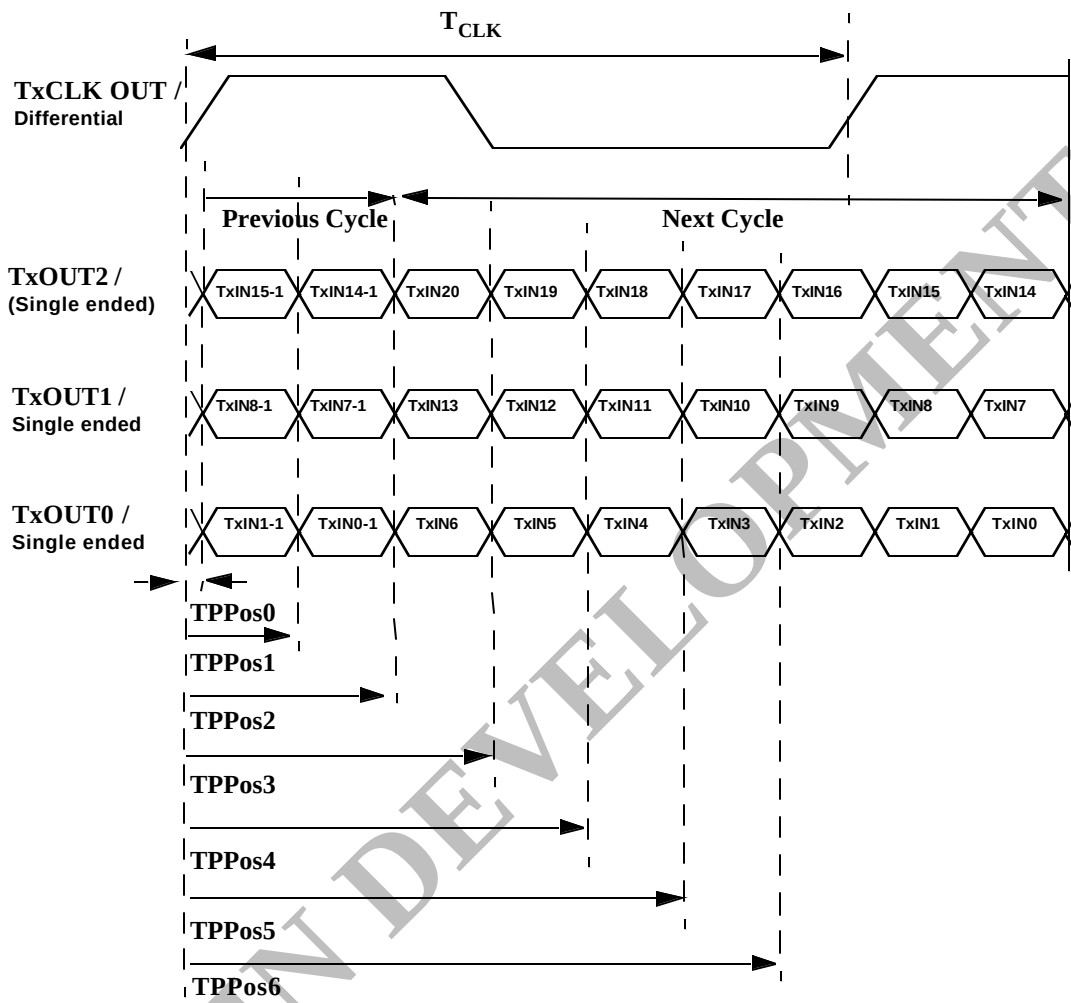


Figure 13. LVDS Output Pulse Position Measurement

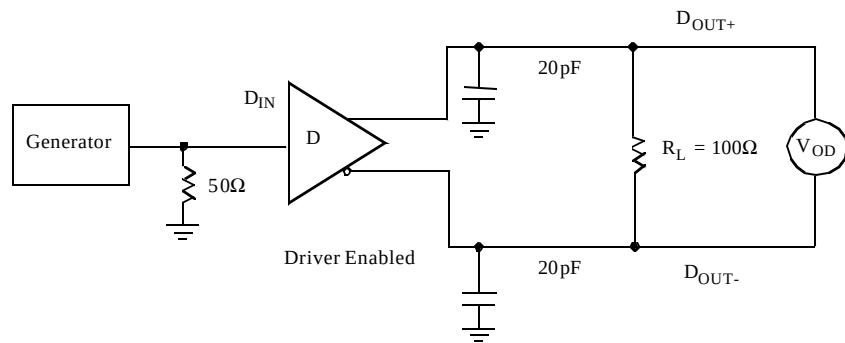
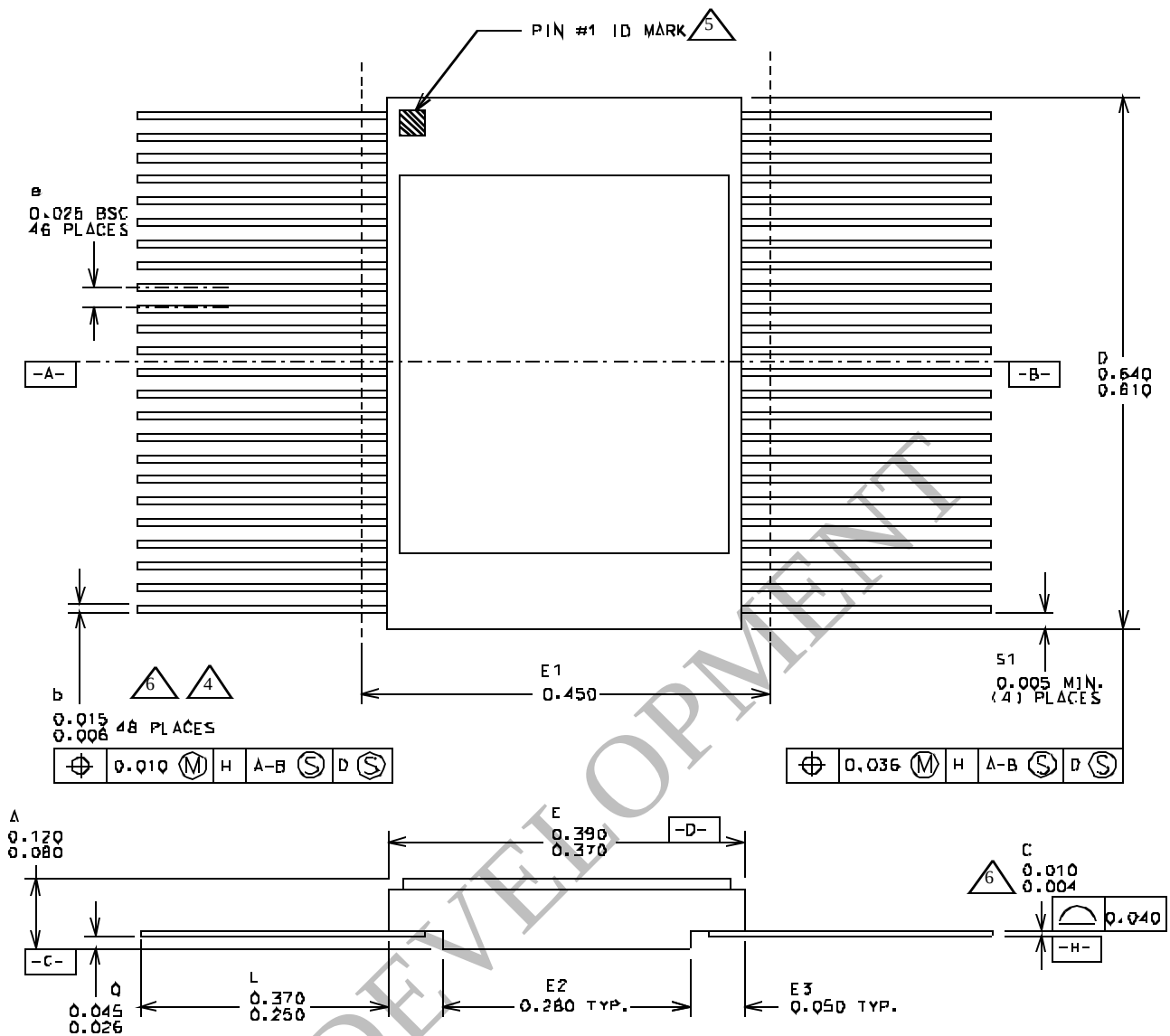


Figure 14. Driver V_{OD} and V_{OS} Test Circuit or Equivalent Circuit

IN DEVELOPMENT

PACKAGING

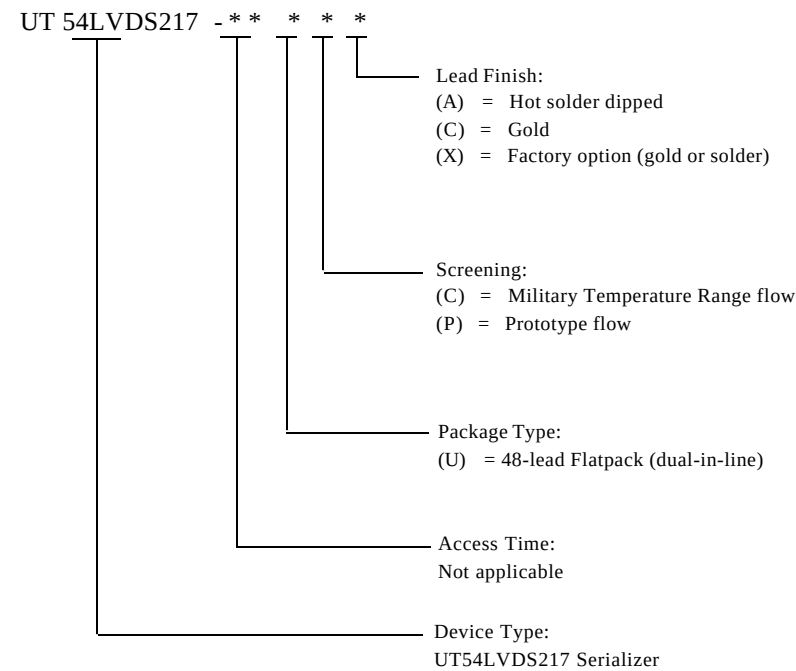


1. All exposed metalized areas are gold plated over electroplated nickel per MIL-PRF-38535.
2. The lid is electrically connected to VSS.
3. Lead finishes are in accordance with MIL-PRF-38535.
4. Lead position and colanarity are not measured.
5. ID mark symbol is vendor option.
6. With solder, increase maximum by 0.003.

Figure 15. 48-Lead Flatpack

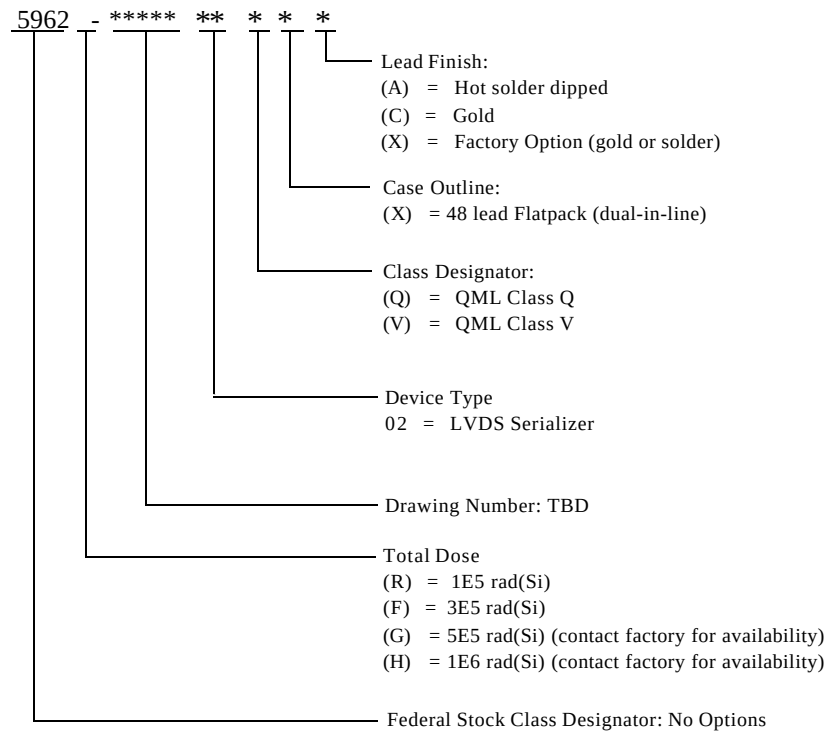
ORDERING INFORMATION

UT54LVDS217 Serializer:



- Notes:**
1. Lead finish (A,C, or X) must be specified.
 2. If an "X" is specified when ordering, then the part marking will match the lead finish and will be either "A" (solder) or "C" (gold).
 3. Prototype flow per UTMCM Manufacturing Flows Document. Tested at 25°C only. Lead finish is GOLD ONLY. Radiation neither tested nor guaranteed.
 4. Military Temperature Range flow per UTMCM Manufacturing Flows Document. Devices are tested at -55°C, room temp, and 125 °C. Radiation neither tested nor guaranteed.

UT54LVDS217 Serializer: SMD



Notes:

1. Lead finish (A, C, or X) must be specified.
2. If an "X" is specified when ordering, part marking will match the lead finish and will be either "A" (solder) or "C" (gold).
3. Total dose radiation must be specified when ordering. QML Q and QML V not available without radiation hardening.